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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	23
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 13x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	28-UFQFN
Supplier Device Package	28-UFQFPN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f031g6u7tr

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

2 Description

The STM32F031x4/x6 microcontrollers incorporate the high-performance ARM[®] Cortex[®]-M0 32-bit RISC core operating at up to 48 MHz frequency, high-speed embedded memories (up to 32 Kbytes of Flash memory and 4 Kbytes of SRAM), and an extensive range of enhanced peripherals and I/Os. All devices offer standard communication interfaces (one I²C, one SPI/ I²S and one USART), one 12-bit ADC,

five 16-bit timers, one 32-bit timer and an advanced-control PWM timer.

The STM32F031x4/x6 microcontrollers operate in the -40 to +85 °C and -40 to +105 °C temperature ranges, from a 2.0 to 3.6 V power supply. A comprehensive set of power-saving modes allows the design of low-power applications.

The STM32F031x4/x6 microcontrollers include devices in six different packages ranging from 20 pins to 48 pins with a die form also available upon request. Depending on the device chosen, different sets of peripherals are included.

These features make the STM32F031x4/x6 microcontrollers suitable for a wide range of applications such as application control and user interfaces, hand-held equipment, A/V receivers and digital TV, PC peripherals, gaming and GPS platforms, industrial applications, PLCs, inverters, printers, scanners, alarm systems, video intercoms and HVACs.

Peripheral STM32F031Fx STM32F031Ex STM32F031Gx STM32F031Kx		STM32	F031Cx							
Flash mem	ory (Kbyte)	16	32	32	16	32	16	32	16	32
SRAM	(Kbyte)					4				
Timoro	Advanced control				1	(16-bit)				
General 4 (16-bit) purpose 1 (32-bit)										
_	SPI [I ² S] ⁽¹⁾		1 [1]							
Comm. I ² C 1										
	USART		1							
12-bit (number of	t ADC f channels)	(9 ext	1 + 3 int.)			(10 e)	1 kt. + 3 int.)			
GP	IOs	1	5	20	2	3	25 (on L 27 (on UF	QFP32) QFPN32)	3	,9
Max. CPU	frequency				48	8 MHz				
Operatin	g voltage				2.0	to 3.6 V				
Operating temperature Ambient operating temperature: -40°C to 85°C / -40°C to 105°C Junction temperature: -40°C to 105°C / -40°C to 125°C)5°C							
Pack	ages	TSSO	OP20	WLCSP25	UFQF	PN28	LQF UFQF	P32 PN32	LQF	[:] P48

Table 2. STM32F031x4/x6 family device features and peripheral counts

1. The SPI interface can be used either in SPI mode or in I^2S audio mode.









3 Functional overview

Figure 1 shows the general block diagram of the STM32F031x4/x6 devices.

3.1 ARM[®]-Cortex[®]-M0 core

The ARM[®] Cortex[®]-M0 is a generation of ARM 32-bit RISC processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM[®] Cortex[®]-M0 processors feature exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The STM32F031x4/x6 devices embed ARM core and are compatible with all ARM tools and software.

3.2 Memories

The device has the following features:

- 4 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states and featuring embedded parity checking with exception generation for fail-critical applications.
- The non-volatile memory is divided into two arrays:
 - 16 to 32 Kbytes of embedded Flash memory for programs and data
 - Option bytes

The option bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protection, debug features (Cortex[®]-M0 serial wire) and boot in RAM selection disabled

3.3 Boot modes

At startup, the boot pin and boot selector option bit are used to select one of the three boot options:

- boot from User Flash memory
- boot from System Memory
- boot from embedded SRAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART on pins PA14/PA15 or PA9/PA10.



DocID025743 Rev 5

In Standby mode, it is put in power down mode. In this mode, the regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption (but the contents of the registers and SRAM are lost).

3.5.4 Low-power modes

The STM32F031x4/x6 microcontrollers support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

Stop mode

Stop mode achieves very low power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low power mode.

The device can be woken up from Stop mode by any of the EXTI lines. The EXTI line source can be one of the 16 external lines, the PVD output, RTC, I2C1 or USART1.

USART1 and I2C1 peripherals can be configured to enable the HSI RC oscillator so as to get clock for processing incoming data. If this is used when the voltage regulator is put in low power mode, the regulator is first switched to normal mode before the clock is provided to the given peripheral.

• Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the RTC domain and Standby circuitry.

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pins, or an RTC event occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering Stop or Standby mode.

3.6 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-32 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example on failure of an indirectly used external crystal, resonator or oscillator).

Several prescalers allow the application to configure the frequency of the AHB and the APB domains. The maximum frequency of the AHB and the APB domains is 48 MHz.



Pinouts and pin description

Figure 5. UFQFPN32 package pinout









			Typical ı	run mode	Typical S	leep mode	unit
Symbol	Parameter	fhclk	Peripheral s enabled	Peripheral s disabled	Peripheral s enabled	Peripheral s disabled	-
		48MHz	20.2	12.3	11.1	2.9	
		36 MHz	15.3	9.5	8.4	2.4	
		32 MHz	13.6	8.6	7.5	2.2	
		24 MHz	10.5	6.7	5.9	1.8	
I	Current	16 MHz	7.2	4.7	4.1	1.4	m۸
'DD	supply	8 MHz	3.8	2.7	2.3	0.9	ША
		4 MHz	2.4	1.8	1.7	0.9	
		2 MHz	1.6	1.3	1.2	0.8	
		1 MHz	1.2	1.1	1.0	0.8	
		500 kHz	1.0	1.0	0.9	0.8	
		48MHz		1	55		
		36 MHz	117				
		32 MHz		1(05		
		24 MHz		8	3		
I	Current	16 MHz		6	0		цΑ
'DDA	supply	8 MHz		2	.2		uA
		4 MHz		2	.2		
		2 MHz		2	.2		1
		1 MHz		2	.2		
		500 kHz		2	.2		

Table 27. Typical current consumption, code executing from Flash memory, running from HSE 8 MHz crystal

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 46: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt



On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 29*. The MCU is placed under the following conditions:

- All I/O pins are in analog mode
- All peripherals are disabled unless otherwise mentioned
- The given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on
- Ambient operating temperature and supply voltage conditions summarized in *Table 15: Voltage characteristics*
- The power consumption of the digital part of the on-chip peripherals is given in *Table 29*. The power consumption of the analog part of the peripherals (where applicable) is indicated in each related section of the datasheet.

Peripheral		Typical consumption at 25 °C	Unit
	BusMatrix ⁽¹⁾	3.8	
	DMA1	6.3	
	SRAM	0.7	
	Flash memory interface	15.2	
	CRC	1.61	
АПБ	GPIOA	9.4	μΑνίνιπΖ
	GPIOB	11.6	
	GPIOC	1.9	
	GPIOF	0.8	
	All AHB peripherals	47.5	

Table 29. Peripheral current consumption



Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



Figure 17. Typical application with a 32.768 kHz crystal

Note: An external resistor is not required between OSC32_IN and OSC32_OUT and it is forbidden to add one.

6.3.8 Internal clock source characteristics

The parameters given in *Table 35* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 18: General operating conditions*. The provided curves are characterization results, not tested in production.



High-speed internal (HSI) RC oscillator

Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
f _{HSI}	Frequency	-	-	8	-	MHz			
TRIM	HSI user trimming step	-	-	-	1 ⁽²⁾	%			
DuCy _(HSI)	Duty cycle	-	45 ⁽²⁾	-	55 ⁽²⁾	%			
		T _A = -40 to 105°C	-2.8 ⁽³⁾	-	3.8 ⁽³⁾				
400	Accuracy of the HSI oscillator	T _A = -10 to 85°C	-1.9 ⁽³⁾	-	2.3 ⁽³⁾				
		T _A = 0 to 85°C	-1.9 ⁽³⁾	-	2 ⁽³⁾	0/			
ACCHSI		$T_A = 0$ to $70^{\circ}C$	-1.3 ⁽³⁾	-	2 ⁽³⁾	70			
		$T_A = 0$ to 55°C	-1 ⁽³⁾	-	2 ⁽³⁾				
		$T_{A} = 25^{\circ}C^{(4)}$	-1	-	1				
t _{su(HSI)}	HSI oscillator startup time	-	1 ⁽²⁾	-	2 ⁽²⁾	μs			
I _{DDA(HSI)}	HSI oscillator power consumption	-	-	80	100 ⁽²⁾	μA			

Table 35. Hol oscillator characteristics	Table 35.	HSI oscillator	[·] characteristics ⁽	1)
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1. V_{DDA} = 3.3 V, T_A = -40 to 105°C unless otherwise specified.

2. Guaranteed by design, not tested in production.

3. Data based on characterization results, not tested in production.

4. Factory calibrated, parts not soldered.



Figure 18. HSI oscillator accuracy characterization results for soldered parts



High-speed internal 14 MHz (HSI14) RC oscillator (dedicated to ADC)

Symbol	Parameter	Conditions Min		Тур	Max	Unit			
f _{HSI14}	Frequency	-	-	14	-	MHz			
TRIM	HSI14 user-trimming step	-	-	-	1 ⁽²⁾	%			
DuCy _(HSI14)	Duty cycle	-	45 ⁽²⁾	-	55 ⁽²⁾	%			
		T _A = -40 to 105 °C	-4.2 ⁽³⁾	-	5.1 ⁽³⁾	%			
	Accuracy of the HSI14 oscillator (factory calibrated)	T _A = −10 to 85 °C	-3.2 ⁽³⁾	-	3.1 ⁽³⁾	%			
ACCHSI14		$T_A = 0$ to 70 °C	-2.5 ⁽³⁾	-	2.3 ⁽³⁾	%			
		T _A = 25 °C	-1	-	1	%			
t _{su(HSI14)}	HSI14 oscillator startup time	-	1 ⁽²⁾	-	2 ⁽²⁾	μs			
I _{DDA(HSI14)}	HSI14 oscillator power consumption	-	_	100	150 ⁽²⁾	μA			

Table 36. HSI14 oscillator characteristics⁽¹⁾

1. V_{DDA} = 3.3 V, T_A = -40 to 105 °C unless otherwise specified.

2. Guaranteed by design, not tested in production.

3. Data based on characterization results, not tested in production.



Figure 19. HSI14 oscillator accuracy characterization results



Symbol	Parameter	Conditions	Min ⁽¹⁾	Unit
N _{END}	Endurance	T _A = -40 to +105 °C	10	kcycle
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 85 °C	30	
		1 kcycle ⁽²⁾ at T _A = 105 °C	10	Year
		10 kcycle ⁽²⁾ at T _A = 55 °C	20	

Table 40. Flash memory endurance and data retention

1. Data based on characterization results, not tested in production.

2. Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 41*. They are based on the EMS levels and classes defined in application note AN1709.

Symbol	Parameter	Conditions	Level/ Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP48, T_A = +25 °C, f _{HCLK} = 48 MHz, conforming to IEC 61000-4-2	2B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP48, T _A = +25°C, f _{HCLK} = 48 MHz, conforming to IEC 61000-4-4	4B

Table 41. EMS characteristics

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.



Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (for example control registers)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Symbol	Parameter	Conditions	Monitored	Max vs. [f _{HSE} /f _{HCLK}]	Unit
Cymbol		Conditions	frequency band	8/48 MHz	onic
		eak level $V_{DD} = 3.6 \text{ V}, \text{ T}_{A} = 25 \text{ °C},$ LQFP48 package compliant with	0.1 to 30 MHz	-11	
\$	Dook lovel		30 to 130 MHz	21	dBµV
S _{EMI} Peak	Feak level		130 MHz to 1 GHz	21	
			EMI Level	4	-

Table 42. EMI characteristics

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts \times (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.





Figure 22. I/O AC characteristics definition

6.3.15 NRST pin characteristics

The NRST pin input driver uses the CMOS technology. It is connected to a permanent pull-up resistor, $\mathsf{R}_{\mathsf{PU}}.$

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 18: General operating conditions*.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{IL(NRST)}	NRST input low level voltage	-	-	-	0.3 V _{DD} +0.07 ⁽¹⁾	V
V _{IH(NRST)}	NRST input high level voltage	-	0.445 V _{DD} +0.398 ⁽¹⁾	-	-	v
V _{hys(NRST)}	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R _{PU}	Weak pull-up equivalent resistor ⁽²⁾	V _{IN} = V _{SS}	25	40	55	kΩ
V _{F(NRST)}	NRST input filtered pulse	-	-	-	100 ⁽¹⁾	ns
V _{NF(NRST)}	NPST input not filtered pulse	$2.7 < V_{DD} < 3.6$	300 ⁽³⁾	-	-	ne
		2.0 < V _{DD} < 3.6	500 ⁽³⁾	-	-	113

 Table 49. NRST pin characteristics

1. Data based on design simulation only. Not tested in production.

2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (~10% order).

3. Data based on design simulation only. Not tested in production.



Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



7.2 LQFP32 package information

LQFP32 is a 32-pin, 7 x 7 mm low-profile quad flat package.



Figure 34. LQFP32 package outline

1. Drawing is not to scale.



Symbol		millimeters		inches ⁽¹⁾			
Symbol	Min	Тур	Мах	Min	Тур	Мах	
А	-	-	1.600	-	-	0.0630	
A1	0.050	-	0.150	0.0020	-	0.0059	
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571	
b	0.300	0.370	0.450	0.0118	0.0146	0.0177	
с	0.090	-	0.200	0.0035	-	0.0079	
D	8.800	9.000	9.200	0.3465	0.3543	0.3622	
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835	
D3	-	5.600	-	-	0.2205	-	
E	8.800	9.000	9.200	0.3465	0.3543	0.3622	
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835	
E3	-	5.600	-	-	0.2205	-	
е	-	0.800	-	-	0.0315	-	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295	
L1	-	1.000	-	-	0.0394	-	
k	0°	3.5°	7°	0°	3.5°	7°	
CCC	-	-	0.100	-	-	0.0039	

1. Values in inches are converted from mm and rounded to 4 decimal digits.



Figure 35. Recommended footprint for LQFP32 package

1. Dimensions are expressed in millimeters.



Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.



Figure 42. UFQFPN28 package marking example

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



7.6 TSSOP20 package information

TSSOP20 is a 20-lead thin shrink small-outline, 6.5 x 4.4 mm, 0.65 mm pitch, package.





1. Drawing is not to scale.

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	-	-	1.200	-	-	0.0472
A1	0.050	-	0.150	0.0020	-	0.0059
A2	0.800	1.000	1.050	0.0315	0.0394	0.0413
b	0.190	-	0.300	0.0075	-	0.0118
С	0.090	-	0.200	0.0035	-	0.0079
D ⁽²⁾	6.400	6.500	6.600	0.2520	0.2559	0.2598
Е	6.200	6.400	6.600	0.2441	0.2520	0.2598
E1 ⁽³⁾	4.300	4.400	4.500	0.1693	0.1732	0.1772
е	-	0.650	-	-	0.0256	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-



Table 07. 1330F20 package mechanical data (continued)						
Symbol	millimeters			inches ⁽¹⁾		
	Min.	Тур.	Max.	Min.	Тур.	Max.
k	0°	-	8°	0°	-	8°
aaa	-	-	0.100	_	_	0.0039

Table 67. TSSOP20 package mechanical data (continued)

1. Values in inches are converted from mm and rounded to four decimal digits.

2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15mm per side.

3. Dimension "E1" does not include interlead flash or protrusions. Interlead flash or protrusions shall not exceed 0.25mm per side.



Figure 47. Recommended footprint for TSSOP20 package

1. Dimensions are expressed in millimeters.



Date	Revision	Changes
16-Dec-2015	4 (continued)	 Section 6.3.16: 12-bit ADC characteristics - changed introductory sentence Table 60: I²S characteristics: table reorganized, t_{v(SD_ST)} max value updated Section 7: Package information: Figure 41: Recommended footprint for UFQFPN28 package updated Section 8: Part numbering: added tray packing to options
06-Jan-2017	5	 Section 6: Electrical characteristics: Table 34: LSE oscillator characteristics (f_{LSE} = 32.768 kHz) - information on configuring different drive capabilities removed. See the corresponding reference manual. Table 22: Embedded internal reference voltage - V_{REFINT} values Figure 26: SPI timing diagram - slave mode and CPHA = 0 and Figure 27: SPI timing diagram - slave mode and CPHA = 1 enhanced and corrected Section 8: Ordering information: The name of the section changed from the previous "Part numbering"

Table 70. Document revision history (continued)

